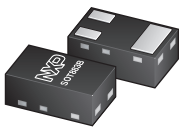


PDTA143EMB

PNP resistor-equipped transistor; R1 = 4.7 kΩ, R2 = 4.7 kΩ

Rev. 1 — 14 May 2012 **Product data sheet**

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC143EMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

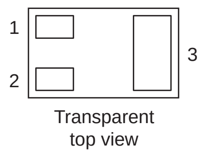
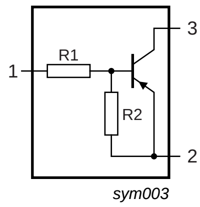
1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
I_O	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T_{amb} = 25 °C	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	 SOT883B (DFN1006B-3)	
2	G	GND (emitter)		
3	O	output (collector)		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PDTA143EMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking

Table 4. Marking codes

Type number	Marking code
PDTA143EMB	0010 0111

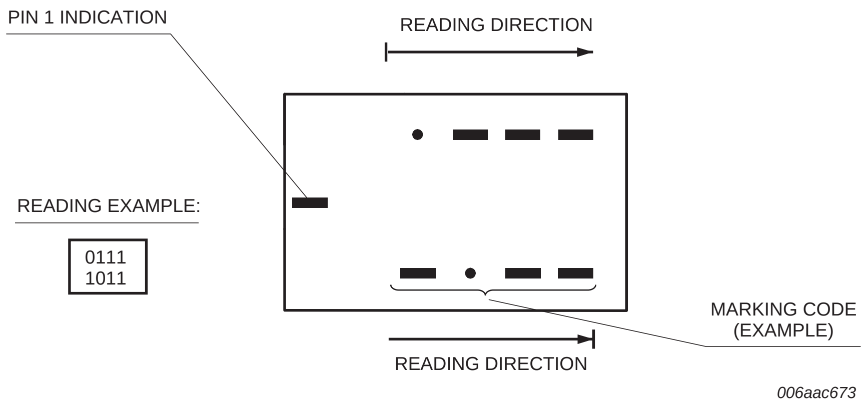


Fig 1. DFN1006B-3 (SOT883B) binary marking code description

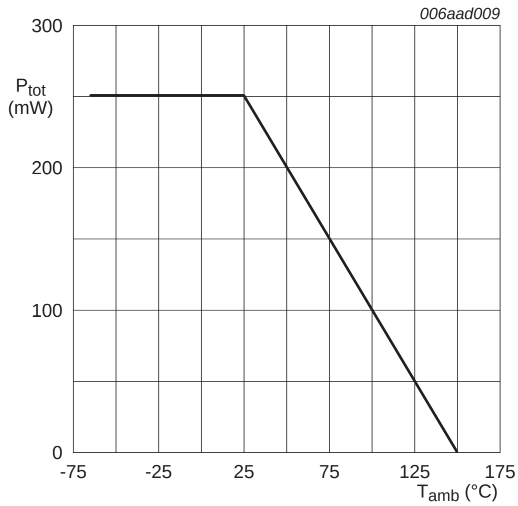
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-50	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V_{EBO}	emitter-base voltage	open collector		-	-10	V
V_I	input voltage	positive		-	10	V
		negative		-	-30	V
I_O	output current			-	-100	mA
I_{CM}	peak collector current	pulsed; $t_p \leq 1$ ms		-	-100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	250	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-65	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

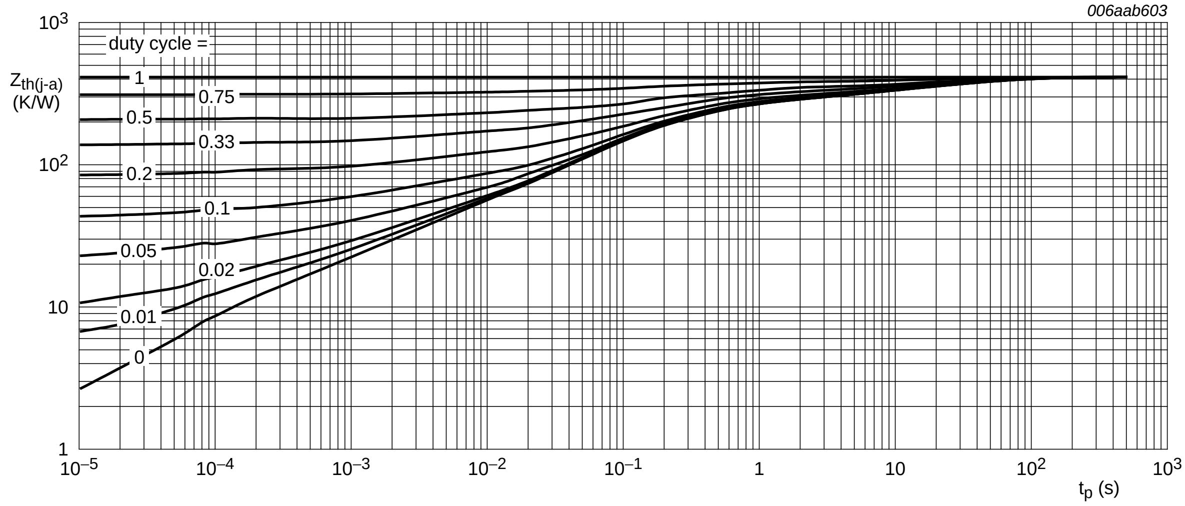
Fig 2. Power derating curve for DFN1006B-3 (SOT883B)

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

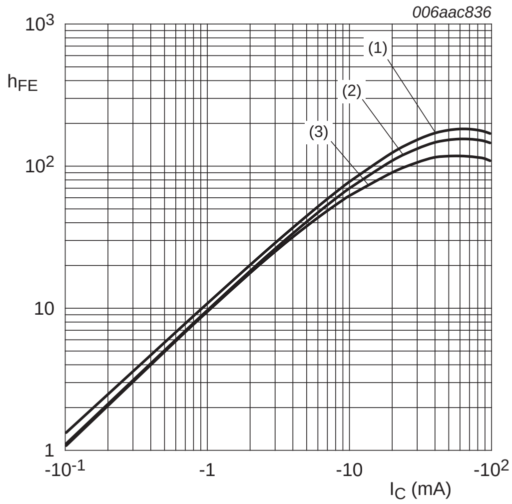
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = -50 V; I_E = 0 A; T_{amb} = 25 °C		-	-	-100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = -30 V; I_B = 0 A; T_{amb} = 25 °C		-	-	-1	µA
		V_{CE} = -30 V; I_B = 0 A; T_j = 150 °C		-	-	-5	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I_C = 0 A; T_{amb} = 25 °C		-	-	-900	µA
h_{FE}	DC current gain	V_{CE} = -5 V; I_C = -10 mA; T_{amb} = 25 °C		30	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C		-	-	-150	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = -5 V; I_C = -100 µA; T_{amb} = 25 °C		-	-1.1	-0.5	V
$V_{I(on)}$	on-state input voltage	V_{CE} = -0.3 V; I_C = -20 mA; T_{amb} = 25 °C		-2.5	-1.9	-	V
R1	bias resistor 1 (input)	T_{amb} = 25 °C		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C_C	collector capacitance	V_{CB} = -10 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF
f_T	transition frequency	V_{CE} = -5 V; I_C = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[1]	-	180	-	MHz

[1] Characteristics of built-in transistor.



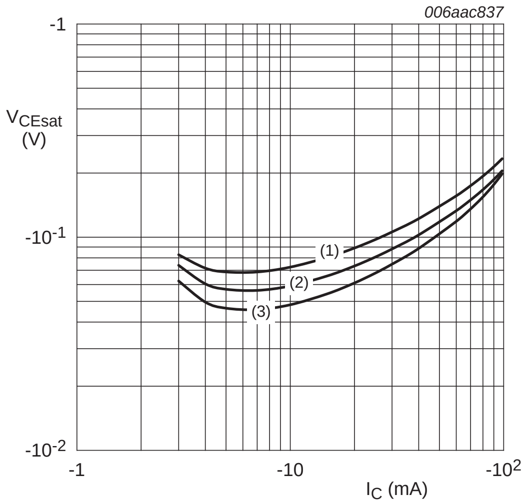
V_{CE} = -5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = -40 °C

Fig 4. DC current gain as a function of collector current; typical values



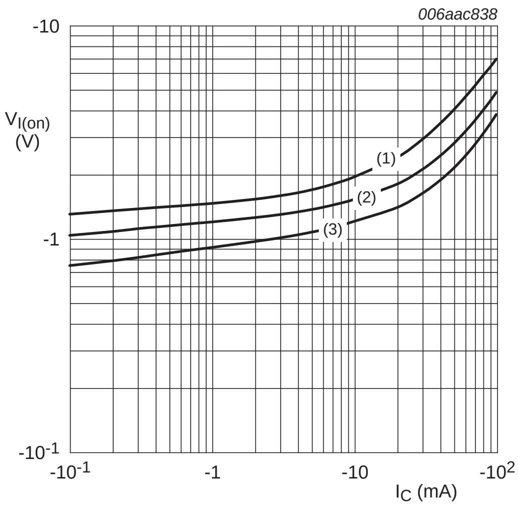
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = -40 °C

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



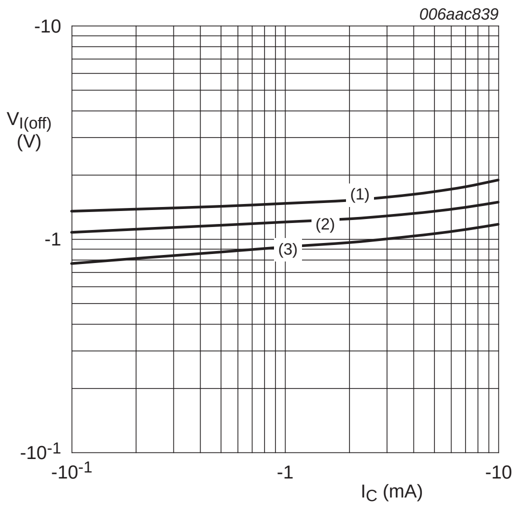
V_{CE} = -0.3 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 6. On-state input voltage as a function of collector current; typical values



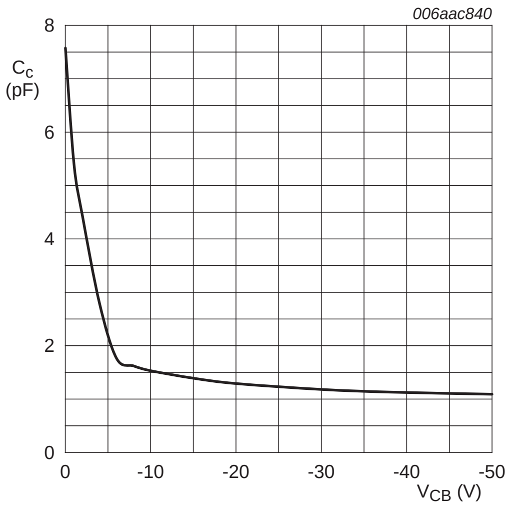
V_{CE} = -5 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

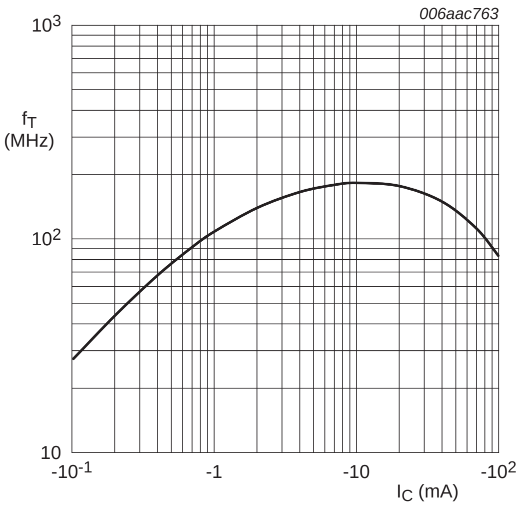
(3) T_{amb} = 100 °C

Fig 7. Off-state input voltage as a function of collector current; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig 8. Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = -5 V; T_{amb} = 25 °C

Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline

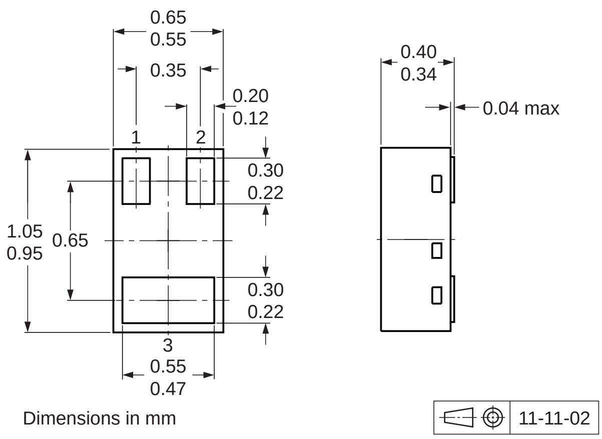


Fig 10. Package outline SOT883B (DFN1006B-3)

10. Soldering

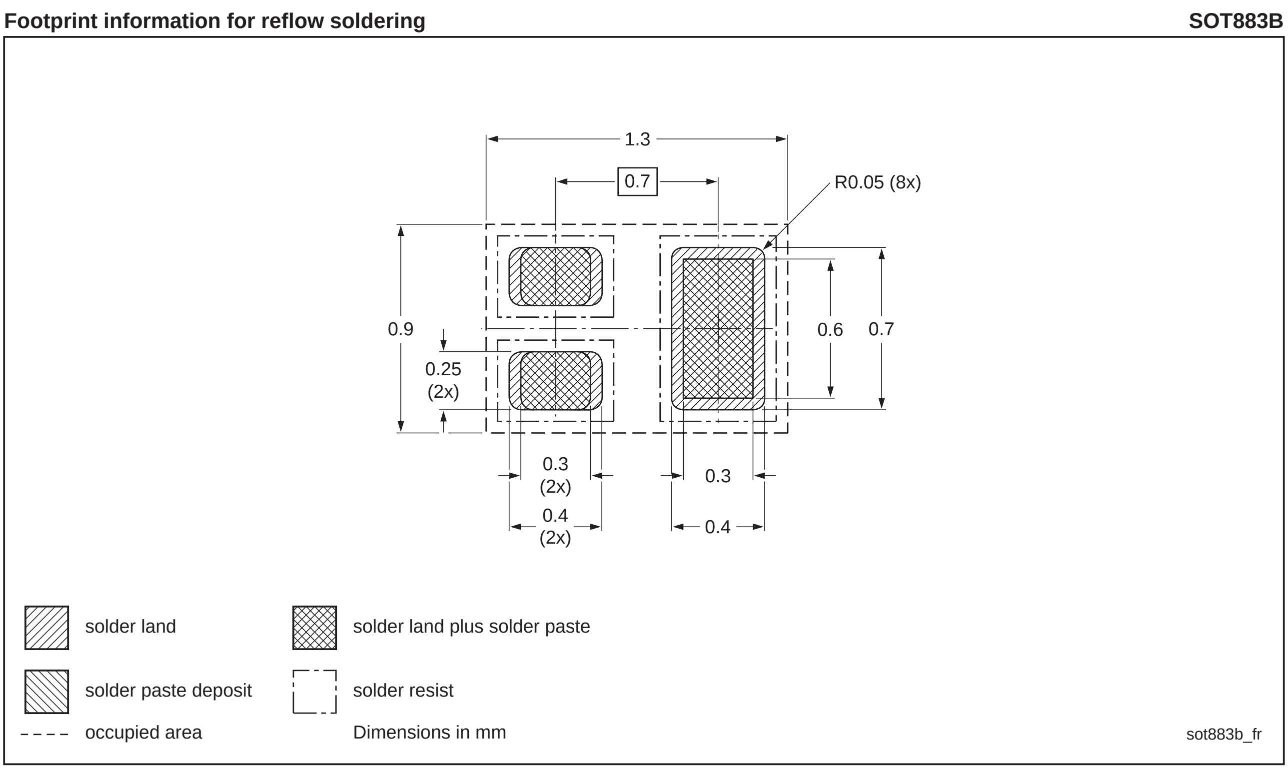


Fig 11. Reflow soldering footprint for SOT883B (DFN1006B-3)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA143EMB v.1	20120514	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

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